

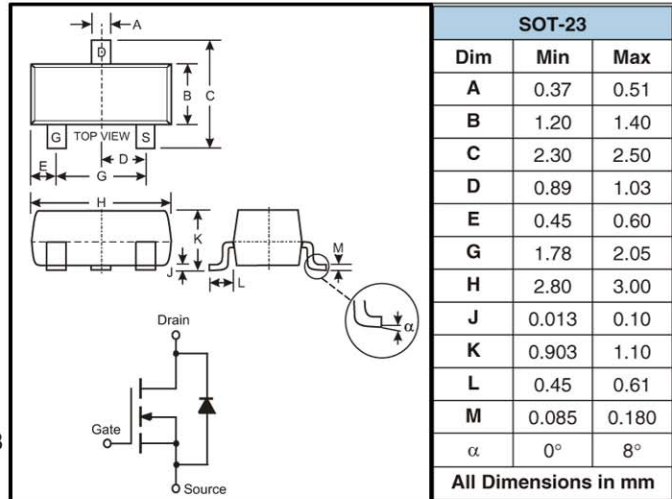
N-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

Features

- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- High Drain-Source Voltage Rating

Mechanical Data

- Case: SOT-23, Molded Plastic
- Case material - UL Flammability Rating 94V-0
- Moisture sensitivity: Level 1 per J-STD-020A
- Terminals: Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Marking: K23 (See Page 3)
- Ordering & Date Code Information: See Page 3
- Weight: 0.008 grams (approx.)



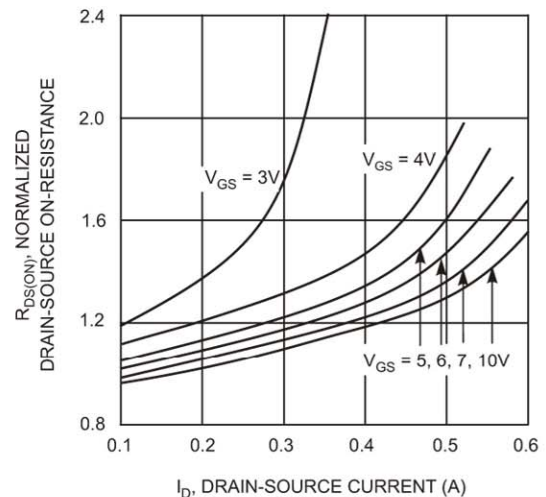
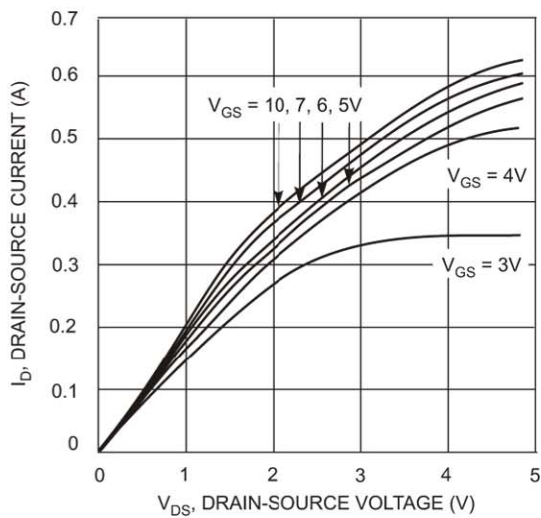
Maximum Ratings @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	BSS123	Units
Drain-Source Voltage	V_{DS}	100	V
Drain-Gate Voltage $R_{GS} \leq 20\text{K}\Omega$	V_{DGR}	100	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current (Note 1)	I_D	170	mA
	I_{DM}	680	
Total Power Dissipation (Note 1)	P_d	300	mW
Thermal Resistance, Junction to Ambient (Note 1)	$R_{\theta JA}$	417	$^\circ\text{C/W}$
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

● Electrical Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 2)						
Drain-Source Breakdown Voltage	BV _{DSS}	100	—	—	V	V _{GS} = 0V, I _D = 250μA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	1.0 10	μA nA	V _{DS} = 100V, V _{GS} = 0V V _{DS} = 20V, V _{GS} = 0V
Gate-Body Leakage, Forward	I _{GSSF}	—	—	50	nA	V _{GS} = 20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 2)						
Gate Threshold Voltage	V _{GS(th)}	0.8	1.4	2.0	V	V _{DS} = V _{GS} , I _D = 1mA
Static Drain-Source On-Resistance	R _{DS (ON)}	— —	— —	6.0 10	Ω	V _{GS} = 10V, I _D = 0.17A V _{GS} = 4.5V, I _D = 0.17A
Forward Transconductance	g _{FS}	80	370	—	mS	V _{DS} = 10V, I _D = 0.17A, f = 1.0KHz
Drain-Source Diode Forward Voltage	V _{SD}	—	0.84	1.3	V	V _{GS} = 0V, I _S = 0.34A
DYNAMIC CHARACTERISTICS						
Input Capacitance	C _{iss}	—	29	60	pF	V _{DS} = 25V, V _{GS} = 0V f = 1.0MHz
Output Capacitance	C _{oss}	—	10	15	pF	
Reverse Transfer Capacitance	C _{rss}	—	2	6	pF	
SWITCHING CHARACTERISTICS						
Turn-On Rise Time	t _r	—	—	8	ns	V _{DD} = 30V, I _D = 0.28A, R _{GEN} = 50Ω, V _{GS} = 10V
Turn-Off Fall Time	t _f	—	—	16	ns	
Turn-On Delay Time	t _{D(ON)}	—	—	8	ns	
Turn-Off Delay Time	t _{D(OFF)}	—	—	13	ns	

Note: 2. Short duration test pulse used to minimize self-heating effect.



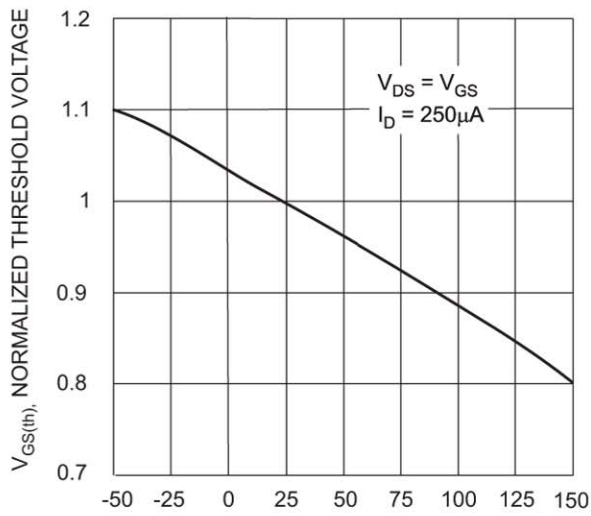


Fig. 3 Gate Threshold Variation with Temperature

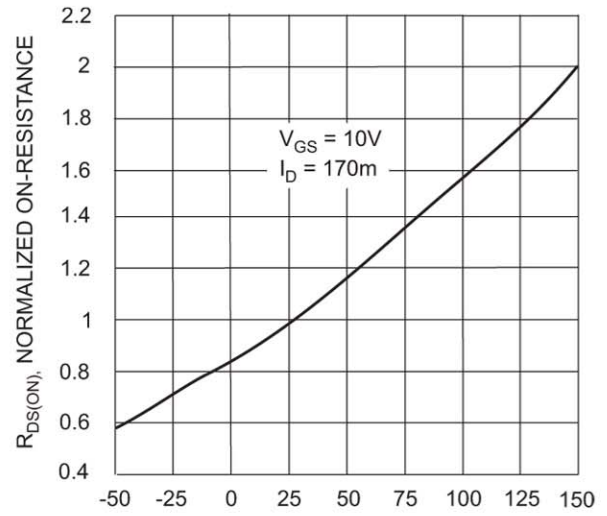


Fig. 4 On-Resistance Variation with Temperature

